

Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)



Complete if Known

Application Number	10/750,061
Filing Date	December 30, 2003
First Named Inventor:	Justin K. Brask, et al.
Art Unit	2812
Examiner Name	Lindsay Jr., Walter Lee
Attorney Docket No.:	42P16680

Sheet 1

of

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
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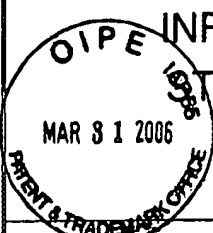
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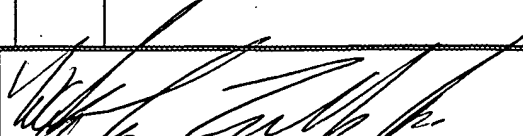
FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
WLL		WO 2004/059726 A1	07-15-2004	IBM Corporation		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
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WLL		International Search Report PCT/US2005/035380, mailed 2/13/2006 (14 pgs.)	
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WLA		WEIZE XIONG, et al., "Improvement of FinFET Electrical Characteristics by Hydrogen Annealing" IEEE Electron Device Letters, Vol. 25, No. 8, August 2004, XP-001198998, pgs. 541-543	
WLL		FU-LIANG YANG, et al., "5nm-Gate Nanowire FinFET" 2004 Symposium on VLSI Technology Digest of Technical Papers, 2004 IEEE, pgs. 196-197	
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Based on Form PTO/SB/08A (08-03) as modified by BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP on 09/10/03.

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WLL		T. TANAKA, et al., "Scalability Study on a Capacitorless 1T-DRAM: From Single-Gate PD-SOI to Double-Gate FinDRAM", 2004 IEEE International Electron Devices Meeting Technical Digest, December 2004, 4 pages.			L
WLL		T. M. MAYER, et al., "Chemical Vapor Deposition of Fluoroalkylsilane Monolayer Films for Adhesion Control in Microelectromechanical Systems" 2000 American Vacuum Society B 18(5), Sep/Oct 2000, pp. 2433-2440			
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